

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	254	(sens\$3 with (contact or electrode) with perforation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:22
L2	202	(sens\$3 near10 (contact or electrode) with perforation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:22
L3	179	(sens\$3 near10 (contact or electrode) near10 perforation)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:22
L4	4	(sens\$3 near10 (contact or electrode) near10 perforation near10 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:23
L5	85	(sens\$3 near10 (contact or electrode) near10 (hole or opening or perforation) near10 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:25
L6	23	(sens\$3 near10 (contact or electrode) near10 (hole or opening or perforation) near10 medium).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:26
L7	2	(sens\$3 near5 layer near10 (contact or electrode) near10 (hole or opening or perforation) near10 medium).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:26
L8	2	(sens\$3 near5 layer near5 (contact or electrode) near10 (hole or opening or perforation) near10 medium).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:26
L9	1	(sens\$3 near5 layer near5 (contact or electrode) near10 (hole or opening or perforation) near5 medium).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:26

L10	2	(sens\$3 near5 layer near5 (contact or electrode) near10 (hole or opening or perforation) near5 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:27
L11	775	(sens\$3 near5 layer near5 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:27
L12	21	(sens\$3 near5 layer near5 property near5 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:28
L13	9	(sens\$3 near layer near5 property near5 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:28
L14	2	(sens\$3 near layer near5 (contact or electrode) near5 property near5 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:29
L15	16	(sens\$3 near layer near5 (contact or electrode) near5 medium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:29
L16	3	(sens\$3 near layer near5 (contact or electrode) near5 medium) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:30
L17	283	(sens\$3 near5 (contact or electrode) near5 medium) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:30
L18	23	(sens\$3 near5 (contact or electrode) near5 medium) and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:30
L19	7	(sens\$3 near5 (contact or electrode) near5 medium);clm. and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:31

L20	33	(sens\$3 near5 (contact or electrode) near5 (fluid or medium)).clm. and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:31
L21	33	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))).clm. and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:31
L22	13	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))).clm. and (ph near level).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:32
L23	2	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))).clm. and (ph near level).clm. and semiconductor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:33
L24	0	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))) with (ph near level).clm. and semiconductor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:33
L25	0	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))) with (ph near level) with semiconductor.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:33
L26	0	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))) with (ph near level) with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:33
L27	51	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))).with.semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:33
L28	2	((sens\$3 near5 (contact or electrode) near5 (fluid or medium))) with semiconductor and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:33
L29	3	((sens\$3 near10 (contact or electrode) near5 (fluid or medium))).with.semiconductor and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:34

L30	3	((sens\$3 near10 (contact or electrode) near10 (fluid or medium))) with semiconductor and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:34
L31	5	((sens\$3 near10 (contact or electrode) near10 (fluid or medium or liquid or gas))) with semiconductor and (ph near level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:34
L32	761	((sens\$3 near10 (contact or electrode) near10 (fluid or medium or liquid or gas))) with semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:34
L33	4	((sens\$3 near10 (contact or electrode) near10 (fluid or medium or liquid or gas))) with semiconductor and (ph adj level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:35
L34	163	(semiconducor or semiconducting) near10 sens\$3 near10 device	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:36
L35	96	(semiconducor or semiconducting) near10 sens\$3 near10 device and (medium or liquid or gas or fluid)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:36
L36	25	(semiconducor or semiconducting) near10 sens\$3 near10 device and (medium or liquid or gas or fluid) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:37
L37	6	(semiconducor or semiconducting) near10 sens\$3 near10 device and (medium or liquid or gas or fluid) and ph and ((contact or electrode) near5 sens\$3)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:38
L38	4098	(sens\$3 adj layer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:38
L39	820	(sens\$3 adj layer) near10 (contact or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:38

L40	646	(sens\$3 adj layer) near5 (contact or electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:38
L41	134	((sens\$3 adj layer) near5 (contact or electrode)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:38
L42	20	((sens\$3 adj layer) near5 (contact or electrode)).clm. and (semiconducting or semiconductor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:39
L43	2	((sens\$3 adj layer) near5 (below or top or bottom or under or underneeth or over or above o) near5 (contact or electrode)).clm. and (semiconducting or semiconductor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:40
L44	20	((sens\$3 adj layer) near5 (below or top or bottom or under or underneeth or over or above o) near5 (contact or electrode)) and (semiconducting or semiconductor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:41
L45	14	((sens\$3 adj layer) near2 (below or top or bottom or under or underneeth or over or above o) near5 (contact or electrode)) and (semiconducting or semiconductor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:41
L46	4	((sens\$3 adj layer) near2 (below or top or bottom or under or underneeth or over or above o) near2 (contact or electrode)) and (semiconducting or semiconductor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:41
L47	4	((sens\$3 adj layer) near2 (below or top or bottom or under or underneeth or over or above o) near2 (contact or electrode)) and (semiconducting or semiconductor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:42
L48	13	((sens\$3 adj layer) near2 (below or top or bottom or under or underneeth or over or above o) near2 (contact or electrode)) and (semiconducting or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:42

L49	5	((sens\$3 adj layer) near2 (below or top or bottom or under or underneath or over or above o) near2 (contact or electrode)) and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:47
L50	5	((sens\$3 adj layer) near2 (below or top or bottom or under or underneath or over or above) near2 (contact or electrode)) and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:47
L51	2	((sens\$3 adj layer) near2 (below or bottom or under or underneath) near2 (contact or electrode)) and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:47
L52	2	((sens\$3 adj layer) near5 (below or bottom or under or underneath) near2 (contact or electrode)) and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:47
L53	2	((sens\$3 adj layer) near5 (below or bottom or under or underneath) near5 (contact or electrode)) and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:47
L54	11	((sens\$3 adj layer) near5 (below or bottom or under or underneath) near5 (contact or electrode)) and (semiconducting or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:48
L55	7	((sens\$3 adj layer) near2 (below or bottom or under or underneath) near5 (contact or electrode)) and (semiconducting or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:48
L56	5	((sens\$3 adj layer) near2 (below or bottom or under or underneath) near2 (contact or electrode)) and (semiconducting or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:48
L57	253	((sens\$3 adj layer) near5 (contact or electrode)) and (semiconducting or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:49
L58	50	((sens\$3 adj layer) near5 (contact or electrode)):clm. and (semiconducting or semiconductor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:49

L59	20	((sens\$3 adj layer) near5 (contact or electrode)).clm. and (semiconducting or semiconductor).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:49
L60	2	((sens\$3 adj layer) near5 (contact or electrode)).clm. and (semiconducting or semiconductor).clm. and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:50
L61	10	((sens\$3 adj layer) near5 (contact or electrode)) and (semiconducting or semiconductor).clm. and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:51
L62	2	((sens\$3 adj layer) near5 (contact or electrode)).clm. and (semiconducting or semiconductor).clm. and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:51
L63	5	((sens\$3 adj layer) near5 (contact or electrode)).clm. and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:52
L64	12	((sens\$3 adj (film or layer)) near5 (contact or electrode)).clm. and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:53
L65	12	((sens\$3 adj (film or layer)).clm. near5 (contact or electrode)).clm. and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:53
L66	33	((sens\$3 adj (film or layer)).clm. and (contact or electrode)).clm. and (semiconducting or semiconductor) and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:54
L67	16	((sens\$3 adj (film or layer)).clm. and (contact or electrode)).clm. and (semiconducting or semiconductor).clm. and ph	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:54
L68	5	((sens\$3 adj (film or layer)).clm. and (contact or electrode)).clm. and (semiconducting or semiconductor).clm. and ph.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:54

L69	5	((sens\$3 adj (film or layer)).clm. and (contact or electrode or lead)).clm. and (semiconducting or semiconductor).clm. and ph.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:55
L70	7	((sens\$3 adj (film or layer)).clm. and (contact or electrode or lead)).clm. and (semiconducting or semiconductor) and ph.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:55
L71	2	((sens\$3 adj (film or layer)).clm. and (contact or electrode or lead)).clm. and (semiconducting or semiconductor) and (ph adj level)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/06 01:55